FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Attorney Docket Number: 5308-156	Serial No.: 09/911,995
	Applicants: Ryu et al.	
	Filing Date: July 24, 2001	Group: 2811

U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
GM	1	6,767,843	07/27/04	Lipkin et al.	438	758	
	2	6,759,684	07/06/04	Fukuda et al.	257	77	
	3	6,653,659	11/25/03	Ryu et al.	257	77	
	4	6,551,865	04/22/03	Kumar et al.	438	137	
	5	6,429,041	08/06/02	Ryu et al.	438	105	
	6	6,303,508	10/16/01	Alok	438	705	
	7	6,297,100	10/02/01	Kumar et al.	438	268	
	8	6,180,958	01/30/01	Cooper, Jr.	257	77	
	9	6,133,587	10/17/00	Takeuchi et al.	257	77	
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	~~39~~	~~EP 1 058 317 A2~~	~~12/06/00~~	~~EPO~~			
	40	JP 01117363	05/10/89	Japan			Abstract
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